

UTC UNISONIC TECHNOLOGIES CO., LTD

2N7002T **Power MOSFET**

300mA, 60V N-CHANNEL POWER MOSFET

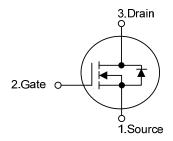
DESCRIPTION

The UTC 2N7002T uses advanced technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with low gate voltages. This device is suitable for use as a load switch or in PWM applications.

FEATURES

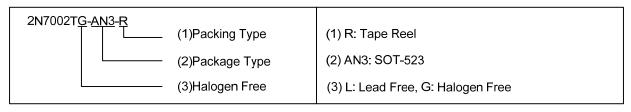
- * High Density Cell Design for Low R_{DS(ON)}.
- * Voltage Controlled Small Signal Switch
- * Rugged and Reliable
- * High Saturation Current Capability

SYMBOL

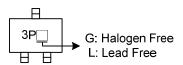


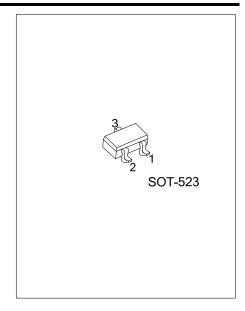
ORDERING INFORMATION

Ordering Number		Dookogo	Pin Assignment			Dooking	
Lead Free	Halogen Free	Package	1	2	3	Packing	
2N7002TL-AN3-R	2N7002TG-AN3-R	SOT-523	S	G	D	Tape Reel	



MARKING





2N7002T Power MOSFET

■ ABSOLUTE MAXIMUM RATINGS (T_A=25°C, unless otherwise specified.)

PARAMETER		SYMBOL	RATINGS	UNIT	
Drain-Source Voltage		V_{DSS}	60	V	
Drain-Gate Voltage (R _{GS} ≤1MΩ)		V_{DGR}	60	V	
IGate Source Voltage	Continuous	V	±20	V	
	Non Repetitive(tp<50µs)	V_{GSS}	±40		
Drain Current	Continuous		300	mA	
	Pulsed	I _D	800		
Power Dissipation		В	200	mW	
Derated Above 25°C		P_D	1.6	mW/°C	
Junction Temperature		TJ	+ 150	°C	
Storage Temperature		T _{STG}	-55 ~ +150	°C	

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ_{JA}	625 (Note1)	°C/W

■ ELECTRICAL CHARACTERISTICS (T_A=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT		
OFF CHARACTERISTICS		•		•				
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =10μA	60			V		
Drain-Source Leakage Current	I _{DSS}	V _{DS} =60V, V _{GS} =0V			1	μΑ		
Cata Sauraa Laakaga Current	I_{GSSF}	V _{GS} =20V, V _{DS} =0V			100	nA		
Gate-Source Leakage Current	I _{GSSR} V _{GS} =-20V, V _{DS} =0V				-100	nA		
ON CHARACTERISTICS (Note2)								
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}$, $I_D = 250 \mu A$	1	2.1	2.5	V		
Drain-Source On-Voltage		V _{GS} = 10V, I _D =300mA		0.6 3.75		V		
Drain-Source On-Voltage	$V_{DS (ON)}$	$V_{GS} = 5.0V, I_{D} = 50mA$		0.09	1.5	\ \ \		
Ctatic Duain Course On Besistance	5	V _{GS} =10V, I _D =300mA			13.5	Ω		
Static Drain-Source On-Resistance	R _{DS (ON)}	V _{GS} =5.0V, I _D =50mA			7.5	Ω		
DYNAMIC CHARACTERISTICS								
Input Capacitance	C _{ISS}	V _{DS} =25V,V _{GS} =0V, f=1.0MHz		20	50	pF		
Output Capacitance	Coss			11	25	pF		
Reverse Transfer Capacitance	C _{RSS}			4	5	pF		
T O.: Time -	t _{ON}	V_{DD} =30V, R_L =150 Ω , I_D =200mA,			20	nS		
Turn-On Time		V_{GS} =10V, R_{GEN} =25 Ω			20	113		
Turn-Off Time	t _{OFF}	V_{DD} =30V, R_L =25 Ω , I_D =200mA,			20			
Turr-On Time		V_{GS} =10V, R_{GEN} =25 Ω			20	nS		
DRAIN-SOURCE DIODE CHARACTER	RISTICS AN	D MAXIMUM RATINGS						
Drain-Source Diode Forward Voltage	V_{SD}	V _{GS} =0V, I _S =300mA (Note)		0.88	1.5	V		
Maximum Pulsed Drain-Source Diode	I _{SM}				0.8	Α		
Forward Current					0.0	^		
Maximum Continuous Drain-Source Diode Forward Current	ls				300	mA		

Note: 1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch. Minimum land pad size.

^{2.} Pulse Test: Pulse Width≤300µs, Duty Cycle≤2.0%

Power MOSFET

TEST CIRCUIT AND WAVEFORM

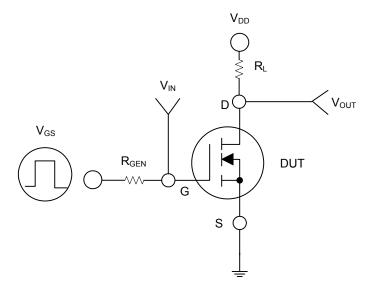


Fig. 1

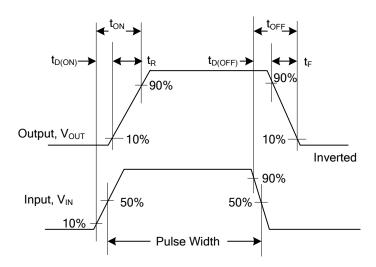


Fig. 2 Switching Waveforms

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